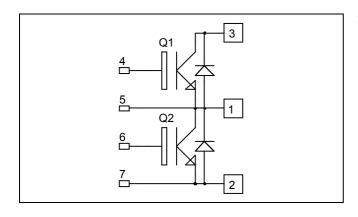
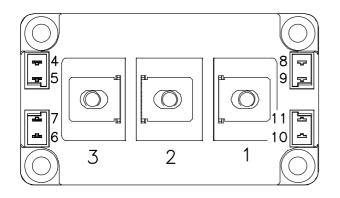


APTGT200A120D3G

Phase leg Trench + Field Stop IGBT3 Power Module





# $V_{CES} = 1200V$ $I_C = 200A$ @ Tc = 80°C

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

#### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- RoHS Compliant

#### Absolute maximum ratings

Syml	ol Parameter	Max ratings	Unit
V <sub>CE</sub>	Collector - Emitter Breakdown Voltage	1200	V
т	Continuous Collector Current $T_c = 25^{\circ}$	C 300	
I <sub>C</sub>	$T_{\rm C} = 80^{\circ}$	C 200	А
I <sub>CN</sub>	Pulsed Collector Current $T_C = 25^{\circ}$	C 400	
$V_{GI}$	Gate – Emitter Voltage	±20	V
PD	Maximum Power Dissipation $T_C = 25^{\circ}$	C 1050	W
RBSC	A Reverse Bias Safe Operating Area $T_j = 125^{\circ}$	°C 400A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



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# All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics								
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				500	μA	
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V	
		$I_{\rm C} = 200 {\rm A}$ $T_{\rm j} = 125^{\circ} {\rm C}$		2.0		v		
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 8mA$		5.0	5.8	6.5	V	
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA	

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$ f = 1MHz			14		nF
C <sub>rss</sub>	Reverse Transfer Capacitance				0.6		m
Q <sub>G</sub>	Gate charge	V <sub>GE</sub> =±15V, I <sub>C</sub> =200A V <sub>CE</sub> =600V			1.9		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			250		
Tr	Rise Time	$V_{GE} = \pm 15V$			90		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 200A$ $R_{G} = 3.6\Omega$			550		ns
$T_{\rm f}$	Fall Time				130		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 200A$ $R_G = 3.6\Omega$			300		ns
T <sub>r</sub>	Rise Time				100		
T <sub>d(off)</sub>	Turn-off Delay Time				650		
$T_{\mathrm{f}}$	Fall Time				180		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		15		mJ
E <sub>off</sub>	Turn off Energy	$I_{\rm C} = 200 \text{A}$ $R_{\rm G} = 3.6 \Omega$	$T_j = 125^{\circ}C$		35		1113
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_i = 125^{\circ}C$			800		А

## Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V
I <sub>RRM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			750	μΑ
I <sub>F</sub>	DC Forward Current		$T_c = 80^{\circ}C$		200	1000	А
V	$V_F$ Diode Forward Voltage $I_F = 200A$ $V_{GE} = 0V$	$I_{\rm F} = 200 {\rm A}$	$T_i = 25^{\circ}C$		1.6	2.1	V
v <sub>F</sub>		$T_{i} = 125^{\circ}C$		1.6		v	
t	Reverse Recovery Time	$I_F = 200A$ $V_R = 600V$ $di/dt = 3500A/\mu s$	$T_j = 25^{\circ}C$		170		100
t <sub>rr</sub>			$T_{j} = 125^{\circ}C$		280		ns
0	Reverse Recovery Charge		$T_j = 25^{\circ}C$		22		чС
Q <sub>rr</sub>			$T_{j} = 125^{\circ}C$		40		μC
E <sub>rr</sub>	Reverse Recovery Energy		$T_j = 25^{\circ}C$		9		mJ
$\mathbf{D}_{\mathrm{ff}}$			$T_{j} = 125^{\circ}C$		16		1115

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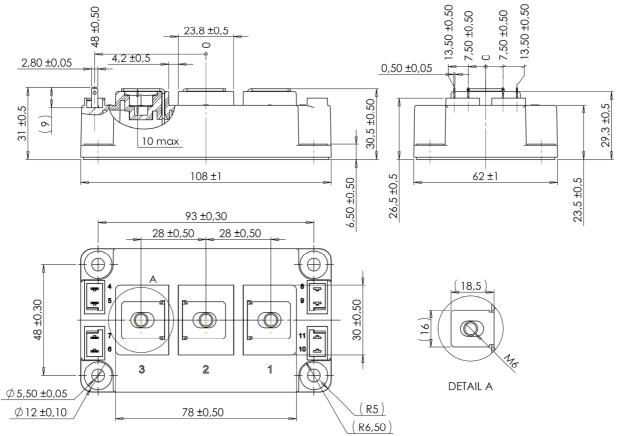


# APTGT200A120D3G

## Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance IGBT Diode		IGBT			0.12	°C/W
<b>R</b> <sub>th</sub> JC			Diode			0.20	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range			-40			125
T <sub>C</sub>	Operating Case Temperature			-40			125
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

## D3 Package outline (dimensions in mm)





#### **Typical Performance Curve**

400

300

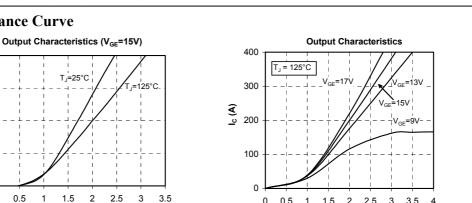
200

100

0

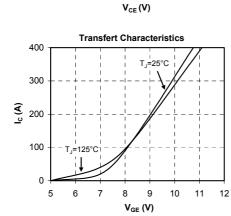
0 0.5

I<sub>c</sub> (A)



0 0.5 1 1.5 2 2.5 3 3.5 4

**APTGT200A120D3G** 

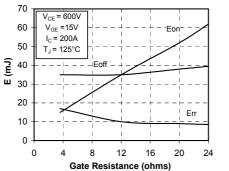


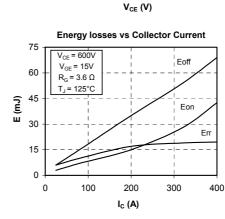
TJ=25°C

1.5 2 2.5

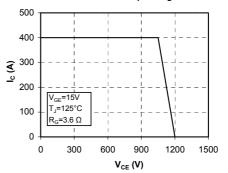
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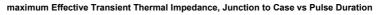
Switching Energy Losses vs Gate Resistance

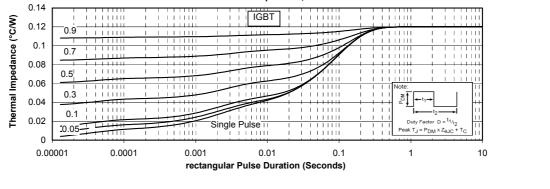




**Reverse Bias Safe Operating Area** 



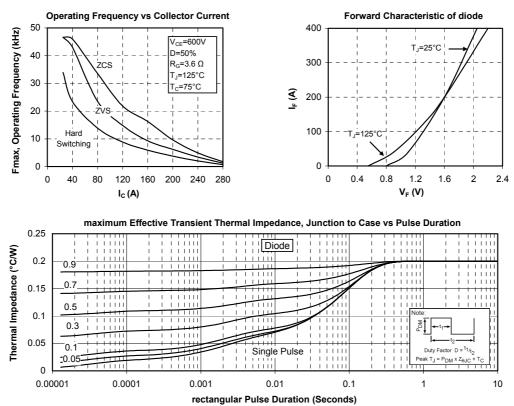




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